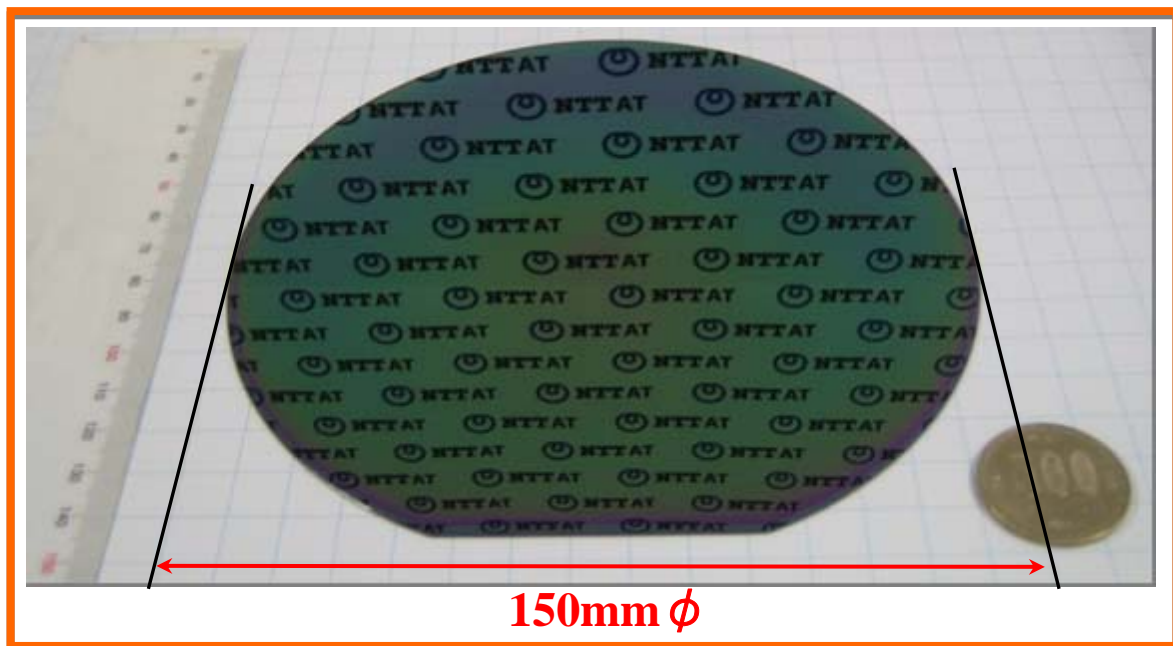
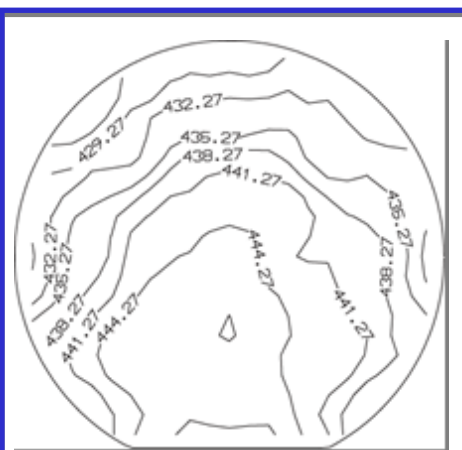


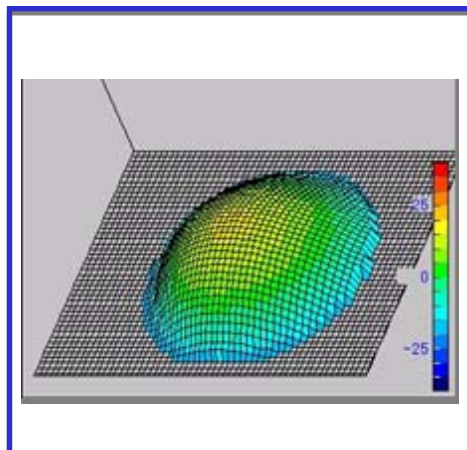
# AlGaIn/GaN HEMT on 6 Inch Si Substrate



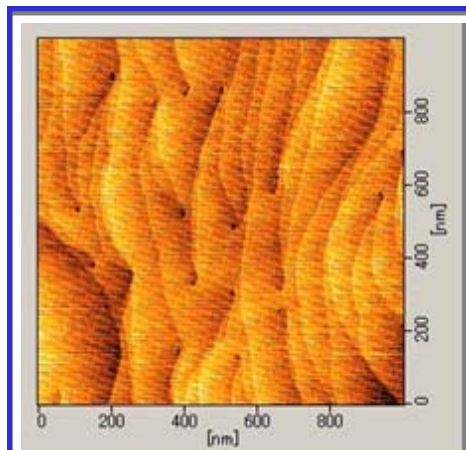
Nitride semiconductors are expected to be the next generation power device. Mass production at low cost calls for a high quality nitride epitaxial wafer on large caliber Si substrate. NTT-AT produces an epitaxial wafer on 6 inch Si substrate with high quality you can trust.



Sheet resistivity distribution:  
Variation 6%  
Ave.:440 ohm/sq.  
Mobility:2180 cm<sup>2</sup>/Vs)



Curvature radius of larger than 160m  
BOW:34  $\mu$ m  
SORI:34  $\mu$ m



Surface roughness: RMS ~0.25 nm  
(1 $\mu$ m field)  
Surface defect density : ~2e9 cm<sup>-2</sup>

※The contents of this catalogue may be changed without previous notification. Also, measured values are not guaranteed value.

For more information:

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